



**ZXTN2011G** 

**100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223** 

#### **Features**

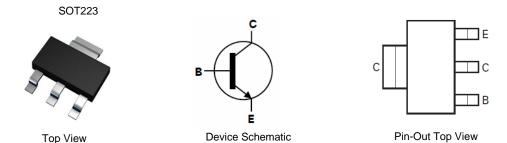
- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 65mV max @ 1A</li>
- $R_{SAT} = 36m\Omega @ I_c = 6A$  for Low Equivalent On-Resistance
- h<sub>FE</sub> Specified up to 10A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

#### Applications

- Line Switching
- Motor Driving (including DC fans)
- High Side Switches
- Subscriber Line Interface Cards (SLIC)



#### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTN2011GTA	ZXTN2011	7	12	1,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

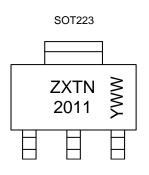
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

Notes:



ZXTN 2011 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	6	A
Peak Pulse Current	I <sub>CM</sub>	10	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W mW/°C	
Linear Derating Factor	(Note 6)	P <sub>D</sub> -	1.6 12.8		
Thermal Desistance Junction to Ambient	(Note 5)	R <sub>θJA</sub>	42		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	78	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	R <sub>0</sub> JL	8.8	7	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

#### ESD Ratings (Note 8)

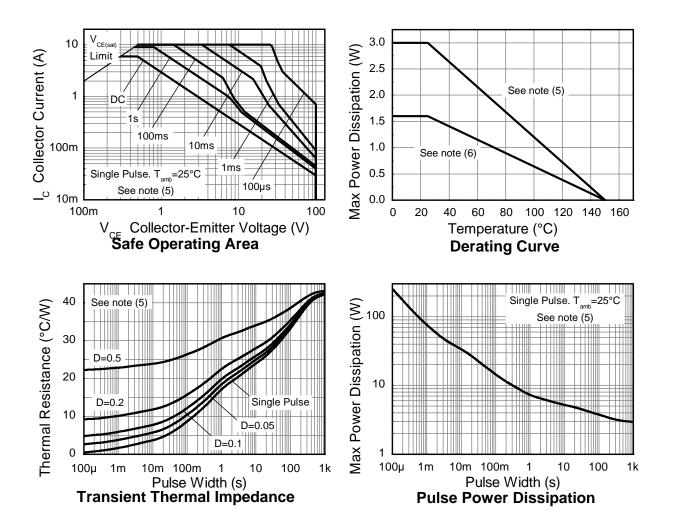
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air For a device mounted with the contector lead on S2mm x 52mm 202 copper that is conditions whilst operating in steady-state.
 Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



#### **ZXTN2011G**

#### **Thermal Characteristics and Derating Information**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

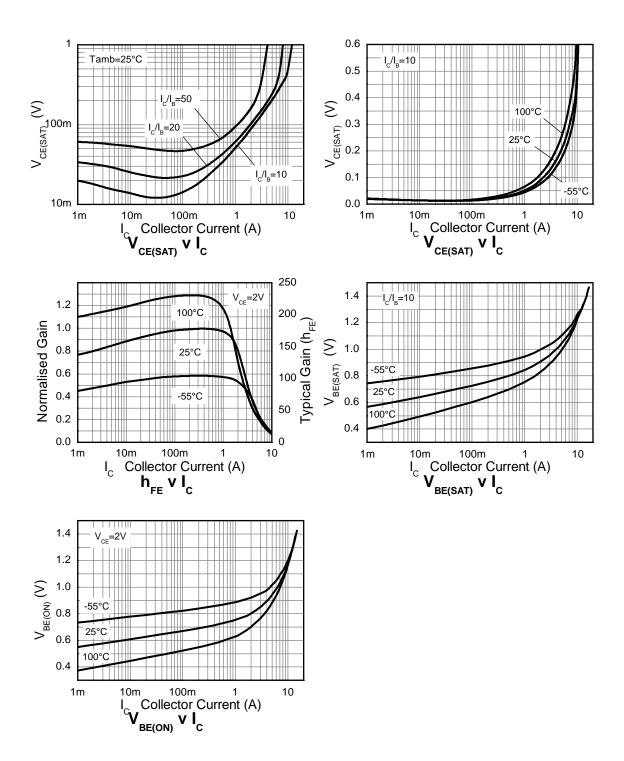
Characteristic	Symbol	Min	Tun	Мах	Unit	Test Condition
	-		Тур			
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	_	V	$I_{C} = 100\mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	200	235		V	I <sub>C</sub> = 1μA, RB ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	100	115	—	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	—	V	I <sub>E</sub> = 100μA
Collector Cutoff Current	lana	—		50	nA	V <sub>CB</sub> = 150V
	I <sub>CBO</sub>	—	—	0.5	μA	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Collector Cutoff Current	ICER	_		100	nA	V <sub>CB</sub> = 150V
	R≤1kΩ	_	—	0.5	μA	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_		10	nA	$V_{EB} = 6V$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>		21 50 95 190	35 65 125 220	mV	$\begin{split} I_{C} &= 0.1A, \ I_{B} = 5mA \\ I_{C} &= 1A, \ I_{B} = 100mA \\ I_{C} &= 2A, \ I_{B} = 100mA \\ I_{C} &= 5A, \ I_{B} = 500mA \end{split}$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>		1.02	1.12	V	$I_{C} = 5A, I_{B} = 500mA$
Base-Emitter Turn-on Voltage (Note 9)	V <sub>BE(on)</sub>	_	0.92	1	V	$I_{C} = 5A, V_{CE} = 2V$
DC Current Gain (Note 9)	hFE	100 100 30 10	230 200 60 20	 300 		$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 5 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 10 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Transition Frequency	f⊤	—	130	—	MHz	$V_{CE} = 10V$ , $I_C = 100mA$ , f = 50MHz
Output Capacitance (Note 9)	Cobo	_	26	—	pF	$V_{CB} = 10V, f = 1MHz$
Quitakina Timan	t <sub>ON</sub>	_	41	_		$V_{CC} = 10V, I_{C} = 1A,$
Switching Times	t <sub>OFF</sub>	_	1,010	—	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



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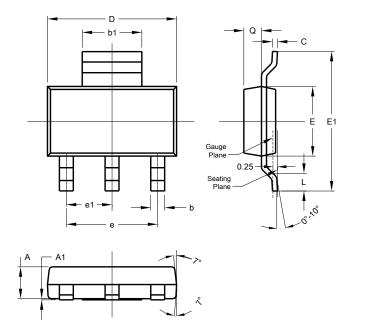
### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





### **Package Outline Dimensions**

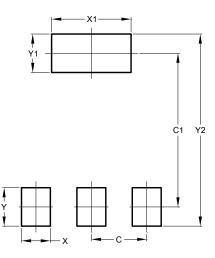
Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
E	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All I	All Dimensions in mm					

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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